

# **isc Silicon NPN Power Transistor**

# 2SC4559

#### **DESCRIPTION**

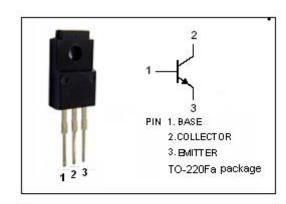
- · Collector-Base Breakdown Voltage-
  - : V<sub>(BR)CBO</sub>= 500V(Min.)
- · High Speed Switching
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

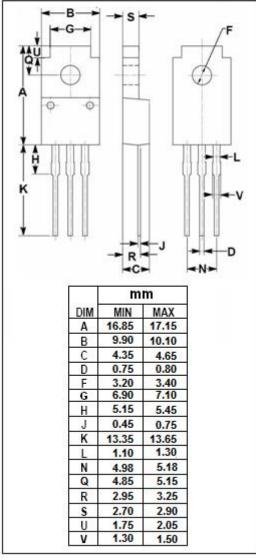
### **APPLICATIONS**

· Designed for high speed switching applications.

# ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	500	V
V <sub>CES</sub>	Collector-Emitter Voltage	500	V
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
Ic	Collector Current-Continuous	7	Α
Ісм	Collector Current-Peak	15	Α
I <sub>B</sub>	Base Current-Continuous	3	Α
Pc	Collector Power Dissipation @T <sub>a</sub> =25℃	2	10/
	Collector Power Dissipation @T <sub>C</sub> =25°C	40	W
Tj	Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$







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#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

10-23 C um	1c-25 C unless otherwise specified									
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	400			٧				
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.6A			1.0	V				
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.6A			1.5	V				
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 500V; I <sub>E</sub> = 0			100	μ <b>A</b>				
ІЕВО	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			100	μ <b>A</b>				
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	10							
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 5V	8							
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V; f= 1MHz		5.5		MHz				
Switching Times										
ton	Turn-on Time				1.0	μS				
ts	Storage Time	I <sub>C</sub> = 3A; I <sub>B1</sub> = 0.6A; I <sub>B2</sub> = -1.2A; V <sub>CC</sub> = 150V			3.0	μS				
t <sub>f</sub>	Fall Time				0.3	μs				

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